



IMT2A

PNP EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE DUAL TRANSISTOR

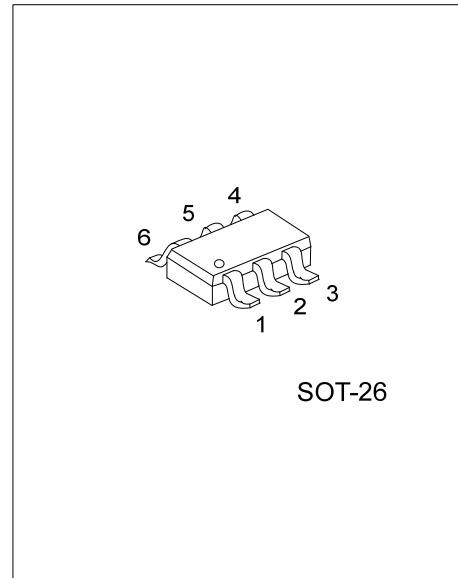
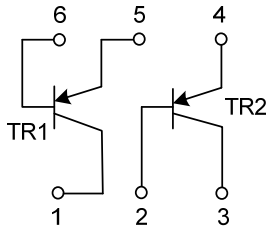
■ DESCRIPTION

The UTC **IMT2A** is a general purpose dual transistor within two chips in a SMT package.

■ FEATURES

* Two MMBT9015 chips in an SMT package.

■ EQUIVALENT CIRCUITS

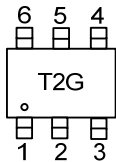


■ ORDERING INFORMATION

Order Number	Package	Pin Description						Packing
		1	2	3	4	5	6	
IMT2AG-AG6-R	SOT-26	C1	B2	C2	E2	E1	B1	Tape Reel

<p>IMT2AG-AG6-R</p> <ul style="list-style-type: none"> (1)Packing Type (2)Package Type (3)Green Package 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) AG6: SOT-26 (3) G: Halogen Free and Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATING ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-150	mA
Collector Power Dissipation (total)	P_C	300(Note)	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

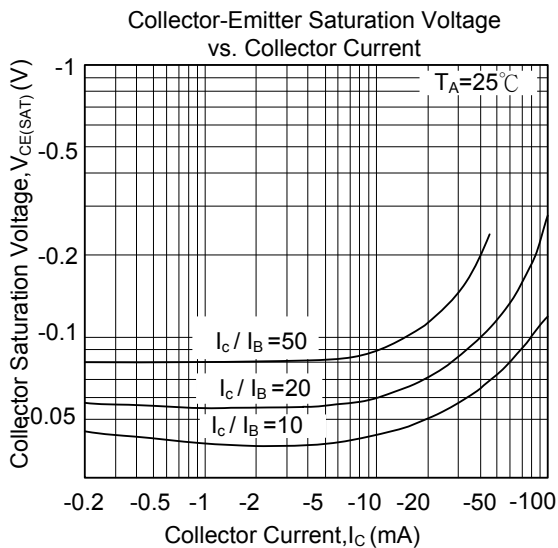
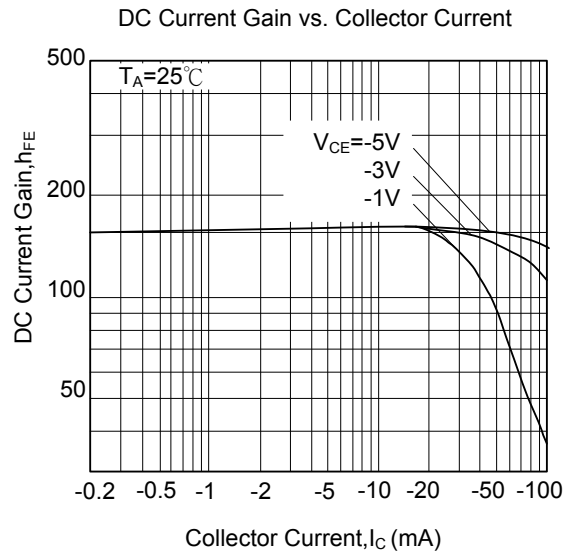
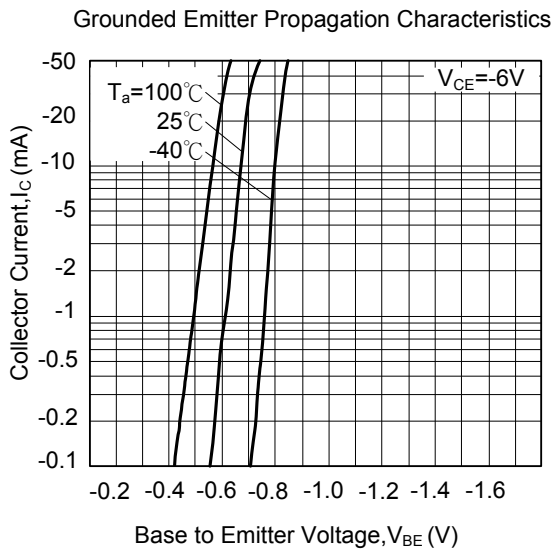
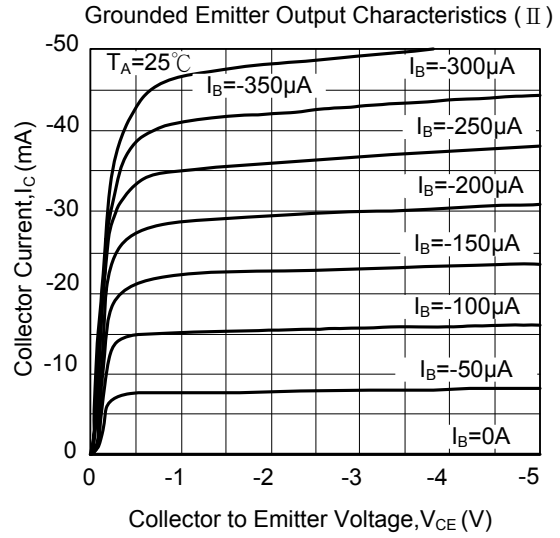
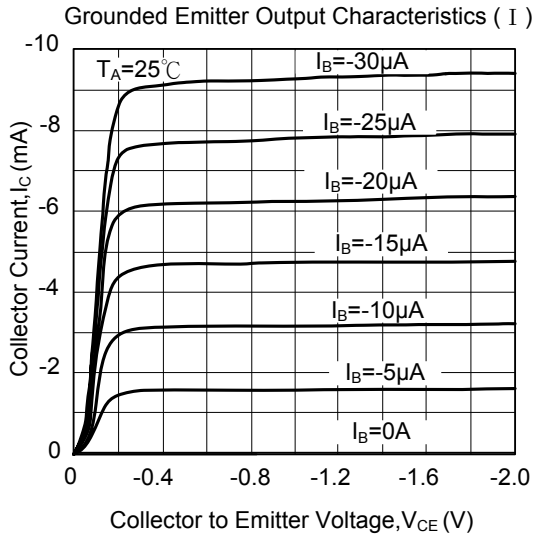
2. 200mW per element must not be exceeded.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to Base Breakdown Voltage	BV_{CBO}	$I_C = -50 \mu\text{A}$	-60			V
Collector to Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1\text{mA}$	-50			V
Emitter to Base Breakdown Voltage	BV_{EBO}	$I_E = -50 \mu\text{A}$	-6			V
Collector Cut Off Current	I_{CBO}	$V_{CB} = -60 \text{V}$			-0.1	μA
Emitter Cut Off Current	I_{EBO}	$V_{EB} = -6 \text{V}$			-0.1	μA
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -50 \text{mA}, I_B = -5 \text{mA}$			-0.5	V
DC Forward Current Gain	h_{FE}	$V_{CE} = -6 \text{V}, I_C = -1\text{mA}$	120		560	
Transition Frequency	f_T	$V_{CE} = -12\text{V}, I_E = 2\text{mA}, f = 100\text{MHz}$ (Note)		140		MHz
Output Capacitance	C_{OB}	$V_{CB} = -12\text{V}, I_E = 0\text{mA}, f = 1\text{MHz}$		4	5	pF

Note: Transition frequency of the device.

TYPICAL CHARACTERISTICS



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